DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2004 Apr 07 2004 Aug 02



PDTA123E series

FEATURES

- · Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

PRODUCT OVERVIEW

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-	-50	V
lo	output current (DC)	-	-100	mA
R1	bias resistor	2.2	-	kΩ
R2	bias resistor	2.2	-	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

	PACKAGE				
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT	
PDTA123EE	SOT416	SC-75	5C	PDTC123EE	
PDTA123EEF	SOT490	SC-89	6C	PDTC123EEF	
PDTA123EK	SOT346	SC-59	42	PDTC123EK	
PDTA123EM	SOT883	SC-101	F7	PDTC123EM	
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES	
PDTA123ET	SOT23	_	*21 ⁽¹⁾	PDTC123ET	
PDTA123EU	SOT323	SC-70	*42 ⁽¹⁾	PDTC123EU	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TYPE NUMBER			DESCRIPTION		
PDTA123ES		PIN 1 2 3	base collector emitter		
PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU	$\begin{array}{c c} & 3 \\ \hline \\ 1 \\ \hline \\ Top view \end{array}$	1 2 3	base emitter collector		
PDTA123EM	2 1 Bottom view 3 1 R1 R2 MDB267 3 MDB267	1 2 3	base emitter collector		

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ORDERING INFORMATION

	PACKAGE			
TYPE NUMBER	NAME	DESCRIPTION	VERSION	
PDTA123EE	-	plastic surface mounted package; 3 leads	SOT416	
PDTA123EEF	_	plastic surface mounted package; 3 leads	SOT490	
PDTA123EK	 plastic surface mounted package; 3 leads SC 		SOT346	
PDTA123EM	-	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883	
PDTA123ES	 plastic single-ended leaded (through hole) package; 3 leads 		SOT54	
PDTA123ET	_	plastic surface mounted package; 3 leads	SOT23	
PDTA123EU	 plastic surface mounted package; 3 leads SOT3 		SOT323	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		_	-12	V
I _O	output current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	_	-	-1	μA
		$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-2	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -20 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	_	_	-150	mV
V _{i(off)}	input-off voltage	$I_{C} = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	-	-1.2	-0.5	V
V _{i(on)}	input-on voltage	$I_{C} = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2	-1.6	-	V
R1	input resistor		1.54	2.2	2.86	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	-	-	3	pF

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PACKAGE OUTLINES















PDTA123E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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